

6MBP15XSFO60-50

IGBT Modules

IGBT MODULE (X series)

600V / 15A / IPM

Features

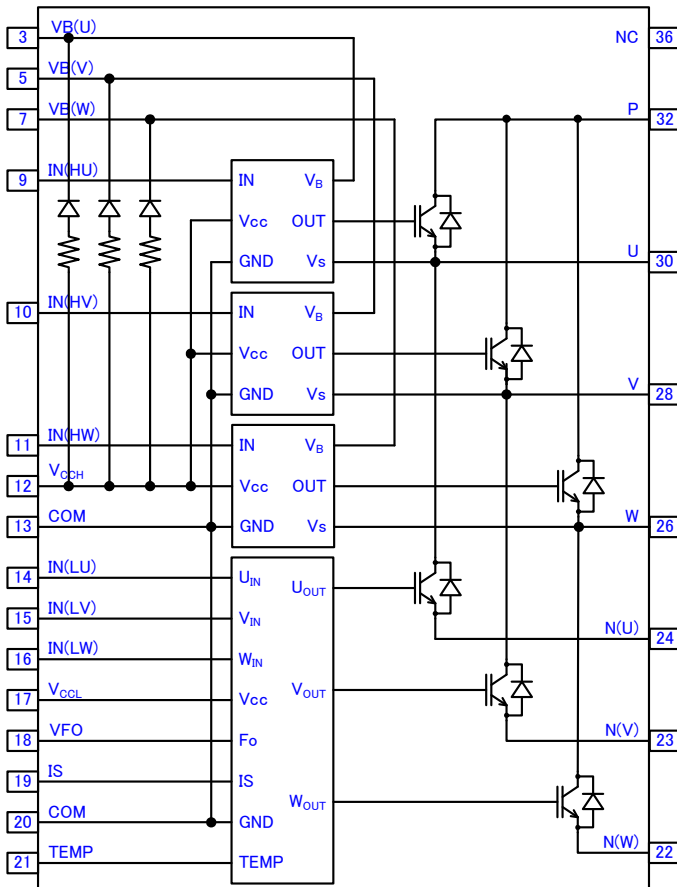
- Low-side IGBTs are separate emitter type
- Short circuit protection
- Temperature sensor output function
- Overheating protection
- Under voltage protection
- Fault signal output function
- Input interface : TTL (3.3V/5V) Active high logic

Applications

AC 100 ~ 240V three phase inverter drive for small power
AC motor drives (such as compressor motor drive for air conditioner, compressor motor drive for heat pump applications, fan motor drive, ventilator motor drive)



Terminal assign and Internal circuit



Pin No.	Pin Name	Pin Description
3	VB (U)	High-side bias voltage for U-phase IGBT driving
5	VB (V)	High-side bias voltage for V-phase IGBT driving
7	VB (W)	High-side bias voltage for W-phase IGBT driving
9	IN (HU)	Signal input for high side U-phase
10	IN (HV)	Signal input for high side V-phase
11	IN (HW)	Signal input for high side W-phase
12	V _{cch}	High-side control supply
13	COM	Common supply ground
14	IN (LU)	Signal input for low side U-phase
15	IN (LV)	Signal input for low side V-phase
16	IN (LW)	Signal input for low side W-phase
17	V _{ccl}	Low-side control supply
18	VFO	Fault output
19	IS	Over current sensing voltage input
20	COM	Common supply ground
21	TEMP	Temperature sensor output
22	N (W)	Negative bus voltage input for W-phase
23	N (V)	Negative bus voltage input for V-phase
24	N (U)	Negative bus voltage input for U-phase
26	W	Motor W-phase output
28	V	Motor V-phase output
30	U	Motor U-phase output
32	P	Positive bus voltage input
36	NC	No Connection

Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$, $V_{cc}=15\text{V}$ (unless otherwise specified)

Items		Symbol	Characteristics	Unit	Remarks
Inverter block	DC Bus Voltage	V _{DC}	450	V	Note *1
	Bus Voltage (Surge)	V _{DC(Surge)}	500	V	Note *1
	Collector-Emitter Voltage	V _{CES}	600	V	
	Collector Current	I _{c@25}	15	A	Note *2
	Peak Collector Current	I _{CP@25}	30	A	V _{CC} ≥15V, V _B (*)≥15V Note *2, *3, *4
			20	A	V _{CC} ≥13V, V _B (*)≥13V Note *2, *3, *4
	Diode Forward current	I _{F@25}	15	A	Note *2
	Peak Diode Forward current	I _{FP@25}	30	A	Note *2
	Collector Power Dissipation	P _{D_IGBT}	32.5	W	per single IGBT T _c =25°C
	FWD Power Dissipation	P _{D_FWD}	25.5	W	per single FWD T _c =25°C
	Junction Temperature	T _j	150	°C	
	Operating Junction Temperature	T _{jOP}	-40 ~ +150	°C	
Control circuit block	High-side Supply Voltage	V _{CCH}	-0.5 ~ 20	V	Applied between V _{CCH} -COM
	Low-side Supply Voltage	V _{CCL}	-0.5 ~ 20	V	Applied between V _{CCL} -COM
	High-side Bias Absolute Voltage	V _{VB(U)-COM} V _{VB(V)-COM} V _{VB(W)-COM}	-0.5 ~ 620	V	Applied between VB(U)-COM, VB(V)-COM, VB(W)-COM
	High-side Bias Voltage for IGBT gate driving	V _{B(U)} V _{B(V)} V _{B(W)}	-0.5 ~ 20	V	Note *4
	High-side Bias offset Voltage	V _U V _V V _W	-5 ~ 600	V	Applied between U-COM, V-COM, W-COM Note *5
	Input Signal Voltage	V _{IN}	-0.5 ~ V _{CCH} +0.5 -0.5 ~ V _{CCL} +0.5	V	Note *6
	Input Signal Current	I _{IN}	3	mA	sink current
	Fault Signal Voltage	V _{FO}	-0.5 ~ V _{CCL} +0.5	V	Applied between V _{FO} -COM
	Fault Signal Current	I _{FO}	1	mA	sink current
	Over Current sensing Input Voltage	V _{IS}	-0.5 ~ V _{CCL} +0.5	V	Applied between I _S -COM
	Junction Temperature	T _j	150	°C	
	Operating Case Temperature	T _C	-40 ~ +125	°C	See Fig.1-1
Storage Temperature	T _{stg}	-40 ~ +125	°C		
Isolation Voltage	V _{iso}	AC 1500	V _{rms}	Sine wave, 60Hz t=1min, Note *7	

Note *1 : Applied between P-N(U), P-N(V), P-N(W)

Note *2 : Pulse width and duty were limited by T_{jmax} .Note *3 : V_{CC} is applied between V_{CCH} -COM, V_{CCL} -COM.Note *4 : $V_{B(*)}$ is applied between $VB(U)$ -U, $VB(V)$ -V, $VB(W)$ -W.Note *5 : Over 13.0V applied between $VB(U)$ -U, $VB(V)$ -V, $VB(W)$ -W. This IPM module might make incorrect response if the high-side bias offset voltage is less than -5V.Note *6 : Applied between $IN(HU)$ -COM, $IN(HV)$ -COM, $IN(HW)$ -COM, $IN(LU)$ -COM, $IN(LV)$ -COM, $IN(LW)$ -COM.

Note *7 : Applied between shorted all terminal and IMS (Insulated Metal Substrate).

Electrical Characteristics

● Inverter block (T_J=25°C unless otherwise specified)

Description	Symbol	Conditions	min.	typ.	max.	Unit
Zero gate Voltage Collector current	I _{CES}	V _{CE} =600V V _{IN} =0V	T _J =25°C	-	-	1 mA
			T _J =125°C	-	-	10 mA
Collector-Emitter saturation Voltage	V _{CE(sat)}	V _{CC} =+15V V _B (*)=+15V V _{IN} =5V Note *4	I _C =1.5A T _J =25°C	-	0.90	1.10 V
			I _C =15A T _J =125°C	-	1.60	1.90
			I _C =15A T _J =125°C	-	1.75	2.10
FWD Forward voltage drop	V _F	I _F =15A V _{IN} =0V	T _J =25°C	-	1.60	1.90 V
			T _J =125°C	-	1.50	-
Turn-on time	t _{on}	V _{DC} =300V I _C =15A V _{CC} =15V V _B (*)=15V T _J =125°C V _{IN} =0V <-> 5V See Fig.2-1 Note *4		0.55	0.90	1.30
Turn-on delay	t _{d(on)}			-	0.75	-
Turn-on rise time	t _r			-	0.15	-
VCE-IC Cross time of turn-on	t _{c(on)}			-	0.35	0.60
Turn-off time	t _{off}			-	0.90	1.30
Turn-off delay	t _{d(off)}			-	0.80	-
Turn-off fall time	t _f			-	0.10	-
VCE-IC Cross time of turn-on	t _{c(off)}			-	0.15	0.30
FWD Reverse Recovery time	t _{rr}			-	0.20	-

● Control circuit block ($T_J=25^\circ\text{C}$ unless otherwise specified)

Description	Symbol	Conditions	min.	typ.	max.	Unit
Circuit current of Low-side	I_{CCL}	$V_{CCL}=15\text{V}$ $V_{IN}=5\text{V}$	-	0.6	0.9	mA
		$V_{CCL}=15\text{V}$ $V_{IN}=0\text{V}$	-	0.6	0.9	
Circuit current of High-side	I_{CCH}	$V_{CCH}=15\text{V}$ $V_{IN}=5\text{V}$	-	1.25	1.9	mA
		$V_{CCH}=15\text{V}$ $V_{IN}=0\text{V}$	-	1.25	1.9	
Circuit current of Bootstrap circuit (per one unit)	I_{CCHB}	$V_B(U)=15\text{V}$, $V_B(V)=15\text{V}$, $V_B(W)=15\text{V}$ $V_{IN}=5\text{V}$	-	-	0.20	mA
		$V_{IN}=0\text{V}$	-	-	0.20	
Input Signal threshold voltage	$V_{th(on)}$	Note *8 $P_w \geq 0.9\mu\text{s}$	-	2.1	2.6	V
	$V_{th(off)}$		0.8	1.3	-	V
Input Signal threshold hysteresis voltage	$V_{th(hys)}$		0.35	0.80	-	V
Operational input pulse width of turn-on	$t_{IN(ON)}$	$V_{IN}=0\text{V}$ to 5V rise up, Note *6, Note *8	0.5	-	-	μs
Operational input pulse width of turn-off	$t_{IN(OFF)}$	$V_{IN}=5\text{V}$ to 0V fall down Note *6, Note *8	0.7	-	-	μs
Input current	I_{IN}	$V_{IN}=5\text{V}$, Note *6	0.7	1.0	1.5	mA
Input pull-down resistance	R_{IN}	Note *6	3.3	5.0	7.2	k Ω
Fault Output Voltage	$V_{FO(H)}$	$V_{IS}=0\text{V}$, VFO terminal pull up to 5V by $10\text{k}\Omega$	4.9	-	-	V
	$V_{FO(L)}$	$V_{IS}=1\text{V}$, $I_{FO}=1\text{mA}$	-	-	0.95	V
Fault Output pulse width	t_{FO}	Note *9, See Fig.2-2, 2-3	20	-	-	μs
Over Current Protection Voltage Level	$V_{IS(ref)}$	$V_{CC}=15\text{V}$ Note *3, *10	0.455	0.48	0.505	V
Over Current Protection Delay time	$t_{d(IS)}$	See Fig.2-2	0.3	0.8	1.3	μs
Output Voltage of temperature sensor	$V_{(temp)}$	Note *11 $T_C=90^\circ\text{C}$	2.63	2.77	2.91	V
		$T_C=25^\circ\text{C}$	0.88	1.13	1.39	V
LVIC Overheating protection	T_{OH}	See Fig.2-6	136	143	150	$^\circ\text{C}$
T_{OH} Hysteresis	$T_{OH(hys)}$		4	10	20	$^\circ\text{C}$
Vcc Under Voltage Trip Level of Low-side	$V_{CCL(OFF)}$	$T_J < 150^\circ\text{C}$ See Fig.2-3	10.3	-	12.5	V
Vcc Under Voltage Reset Level of Low-side	$V_{CCL(ON)}$		10.8	-	13.0	V
Vcc Under Voltage hysteresis	$V_{CCL(hys)}$		-	0.5	-	V
Vcc Under Voltage Trip Level of High-side	$V_{CCH(OFF)}$	$T_J < 150^\circ\text{C}$ See Fig.2-4	8.3	-	10.3	V
Vcc Under Voltage Reset Level of High-side	$V_{CCH(ON)}$		8.8	-	10.8	V
Vcc Under Voltage hysteresis	$V_{CCH(hys)}$		-	0.5	-	V
VB Under Voltage Trip Level	$V_{B(OFF)}$	$T_J < 150^\circ\text{C}$ See Fig.2-5	10.0	-	12.0	V
VB Under Voltage Reset Level	$V_{B(ON)}$		10.5	-	12.5	V
VB Under Voltage hysteresis	$V_{B(hys)}$		-	0.5	-	V
Forward voltage of Bootstrap diode	$V_{F(BSD)}$	$T_J=25^\circ\text{C}$ $I_{F(BSD)}=10\text{mA}$	0.90	1.4	1.90	V
	$V_{F(BSD)}$	$T_J=25^\circ\text{C}$ $I_{F(BSD)}=100\text{mA}$	2.3	4.3	6.3	

Note *8 : This IPM module might make incorrect response if the input signal pulse width is less than $t_{IN(on)}$ and $t_{IN(off)}$.

Note *9: Fault signal is asserted corresponding to an "Over-current protection", an "Under-voltage protection" at low-side, and an "Over-heat protection".

Under the condition of "Over-current protection" or "Under-voltage protection" or "Over-heat protection", the fault signal is asserted continuously while these conditions are continuing. However, the minimum fault output pulse width is minimum $20\mu\text{s}$ even if very short failure condition (which is less than $20\mu\text{s}$) is triggered.

Note *10 : Over current protection is functioning only for the low-side arms.

Note *11 : Fig.1-1 shows the measurement position of temperature sensor.

Thermal Characteristics

Description	Symbol	min.	typ.	max.	Unit
Junction to Case Thermal Resistance (per single IGBT) Note *12	$R_{th(j-c)}_{IGBT}$	-	-	3.85	°C/W
Junction to Case Thermal Resistance (per single FWD) Note *12	$R_{th(j-c)}_{FWD}$	-	-	4.95	°C/W

Note *12: Thermal compound with good thermal conductivity should be applied evenly with about +100μm~+200μm on the contacting surface of this device and heat-sink.

Mechanical Characteristics

Description	Symbol	Conditions	min.	typ.	max.	Unit
Tighten torque	-	Mounting screw: M3	0.59	0.69	0.98	Nm
Heat-sink side flatness	-	Note. *13	0	-	100	μm
Weight	-	-	-	9.3	-	g

Note *13: Fig.1-2 shows the measurement position of heat sink flatness

Recommended Operation Conditions

● All voltages are absolute voltages referenced to Vcc –potential unless otherwise specified.

Description	Conditions	min.	typ.	max.	Unit
DC Bus Voltage	V_{DC}	0	300	400	V
High-side Bias Voltage for IGBT gate driving	$V_B(^*)$	13.0	15.0	18.5	V
High-side Supply Voltage	V_{CCH}	13.5	15.0	16.5	V
Low-side Supply Voltage	V_{CCL}	13.5	15.0	16.5	V
Control Supply variation	ΔV_B	-1	-	1	V/μs
	ΔV_{CC}	-1	-	1	
Input signal voltage	V_{IN}	0	-	5	V
Voltage for current sensing	V_{ISC}	0	-	5	V
Potential difference of between COM to N (including surge)	V_{COM_N}	-5	-	5	V
Dead time for preventing arm-short ($T_c \leq 125^\circ\text{C}$)	t_{DEAD}	1.0	-	-	μs
Allowable output current (Note *14)	I_o	-	-	15.0	A rms
Allowable minimum input pulse width (Note *15, Note *16)	$PW_{IN(on)}$	0.5	-	-	μs
	$PW_{IN(off)}$	0.7	-	-	μs
PWM Input frequency	f_{PWM}	-	-	20	kHz
Operating Junction Temperature	$T_{j(ope)}$	-30	-	150	°C

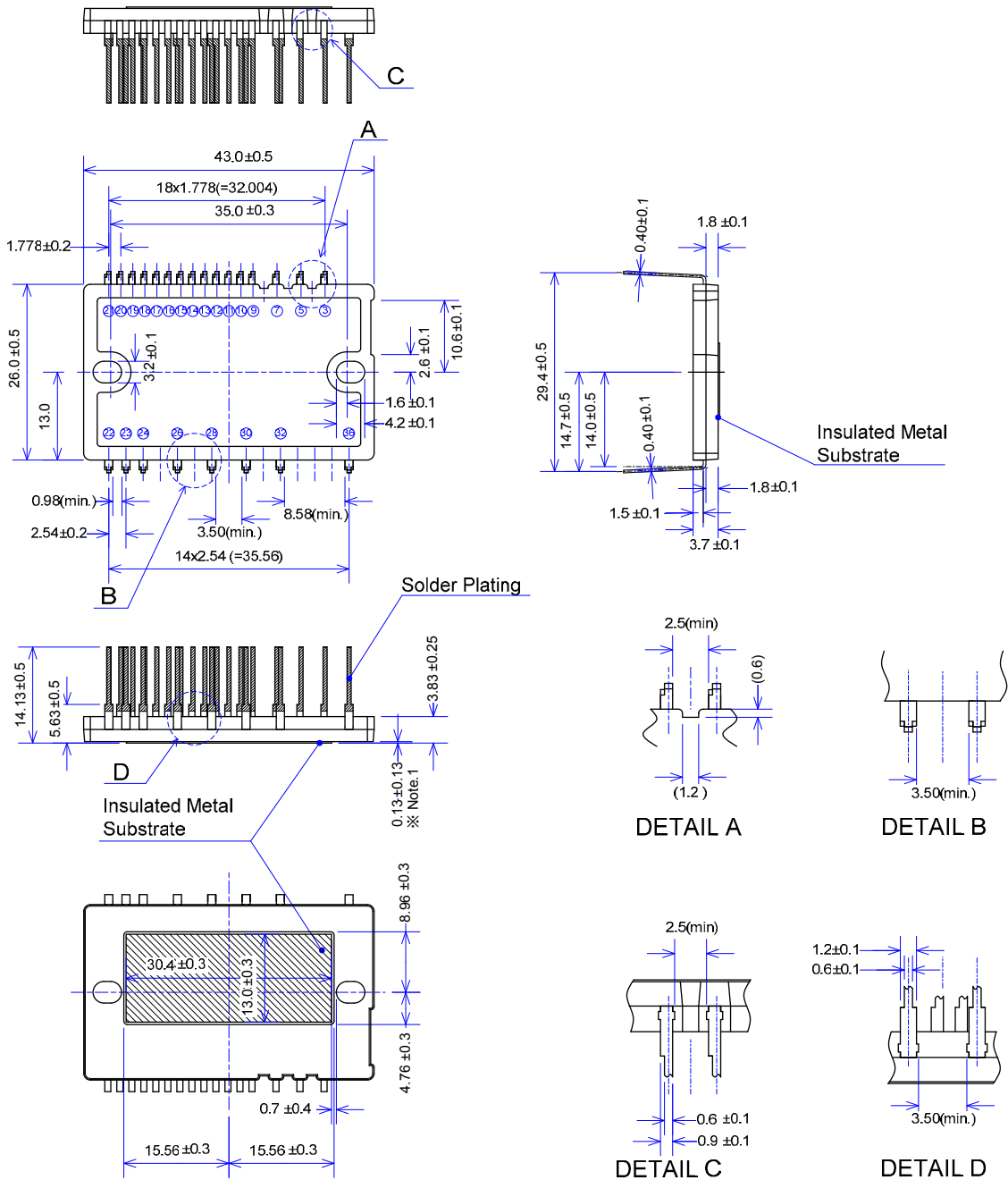
Note *14 : $V_{DC}=300\text{V}$, $V_{CCH}=V_{CCL}=V_B(^*)=15\text{V}$, $\text{PF}=0.8$, Sinusoidal PWM, 3phase modulation, $T_j \leq 150^\circ\text{C}$, $T_c \leq 100^\circ\text{C}$, $f_{PWM}=5\text{kHz}$, $f_o=200\text{Hz}$, $K_s=0.9$

Note *15 : In the pulse width of 0.5μs, the loss of IGBT increases for the saturation operation.

To reduce the loss of IGBT, please enlarge the pulse width more than the switching time of IGBT.

Note *16 : This IPM module might response according to input signal pulse even when the input signal pulse width is less than $PW_{IN(on)}$ and $PW_{IN(off)}$.

Package outline dimensions

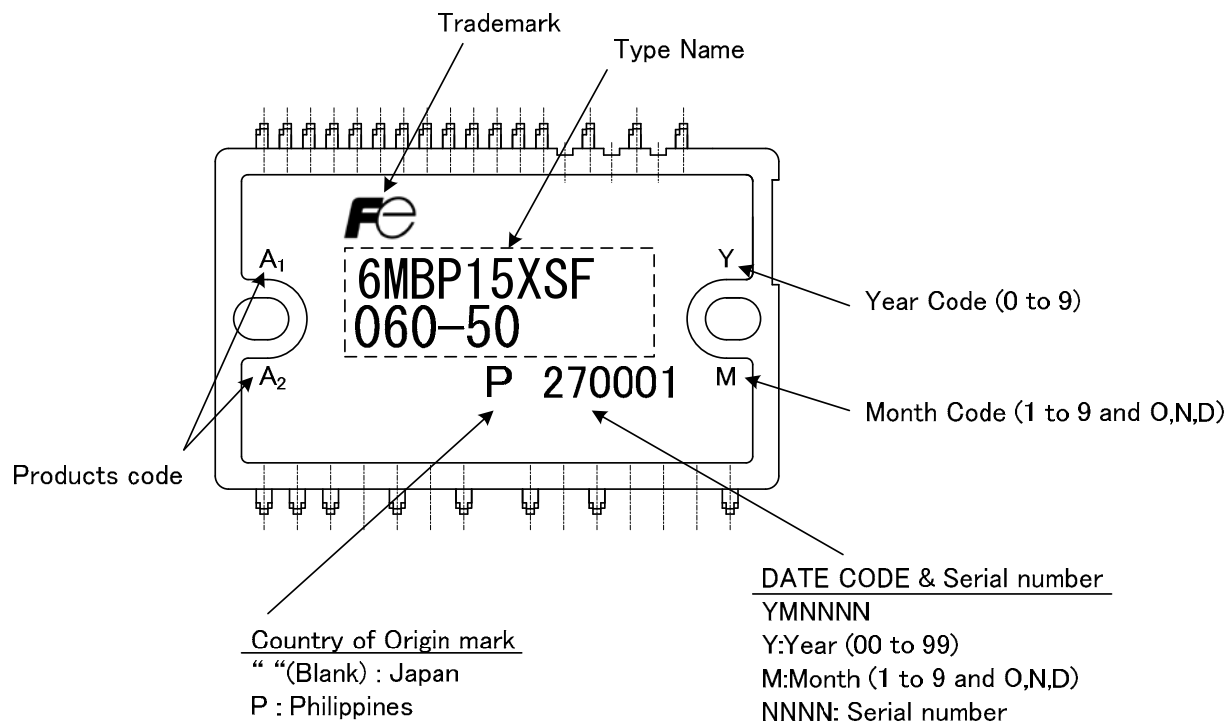


Unit: mm

Note ※1: The IMS(Insulated Metal Substrate) deliberately protruded from back surface of case.
 It is improved of thermal conductivity between IMS and heat-sink.

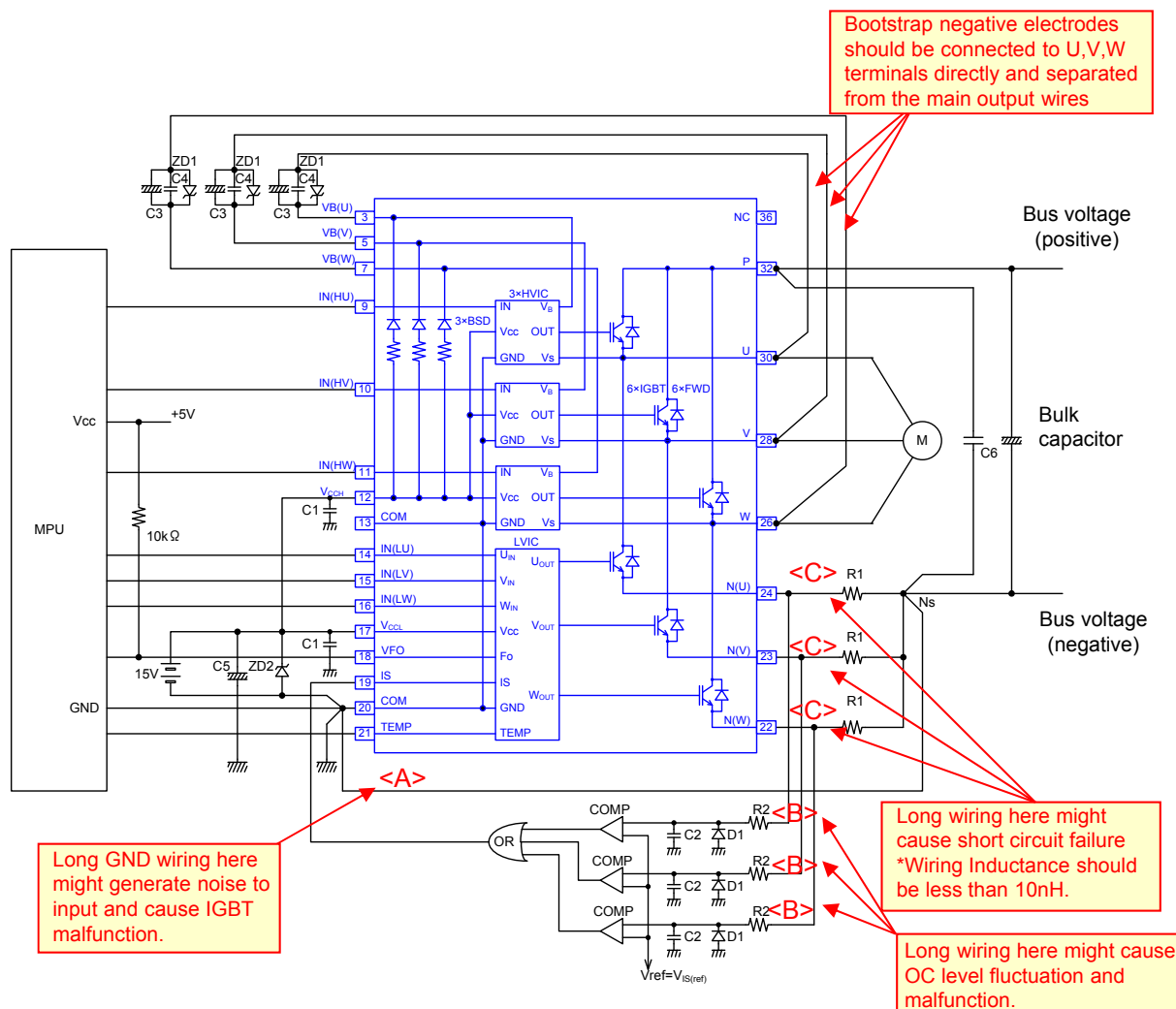
Pin No.	Pin Name	Pin No.	Pin Name	Pin No.	Pin Name
3	VB(U)	14	IN(LU)	22	N(W)
5	VB(V)	15	IN(LV)	23	N(V)
7	VB(W)	16	IN(LW)	24	N(U)
9	IN(HU)	17	V _{CCL}	26	W
10	IN(HV)	18	VFO	28	V
11	IN(HW)	19	IS	30	U
12	V _{CCH}	20	COM	32	P
13	COM	21	TEMP	36	NC

■ Marking



Note : Product code A₁ means current ratings , and “L” is marked.
 Product code A₂ means variations , and “F” is marked.

● Fig. shows an example of an application circuit.



Note *13: If signal GND is connected to power GND by broad pattern, it may cause malfunction by power GND fluctuation. It is recommended to connect signal GND and power GND at only a point.

Fig.1-1: The measurement position of temperature sensor.

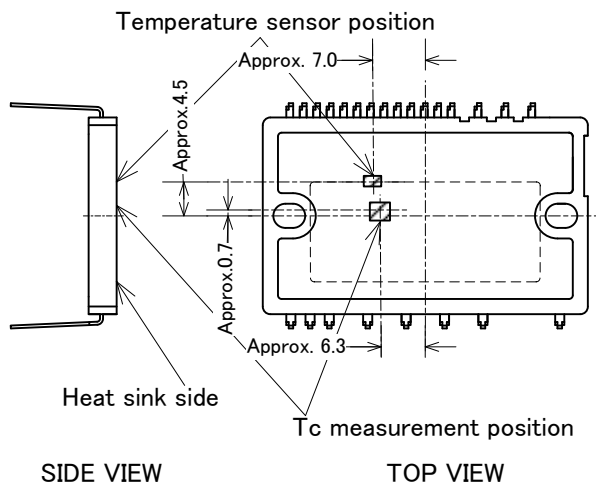


Fig.1-2: The measurement position of heat sink flatness

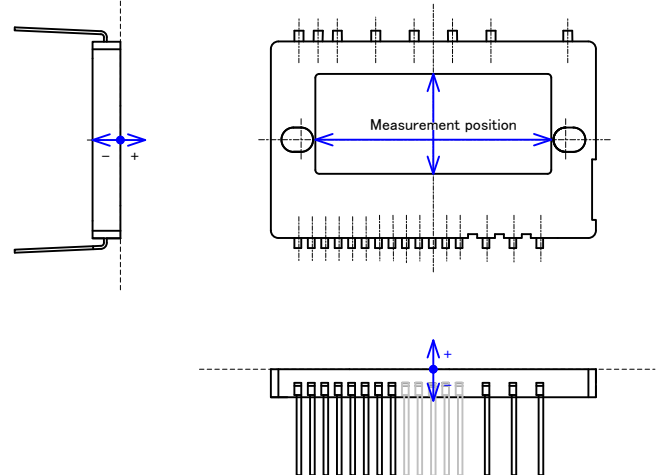


Fig.2-1: Switching waveforms

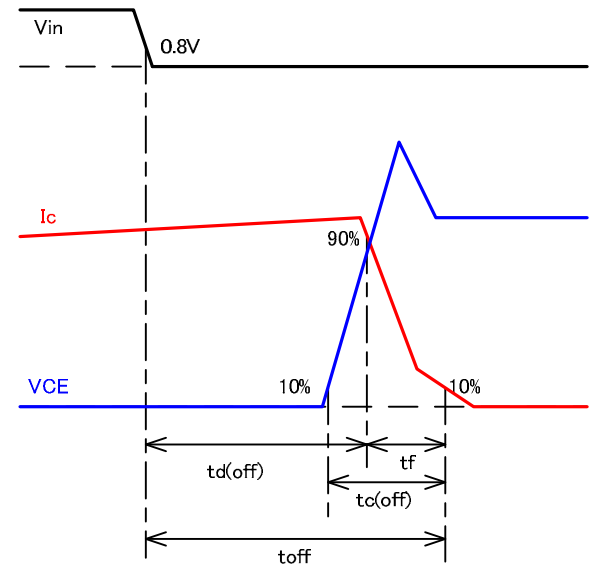
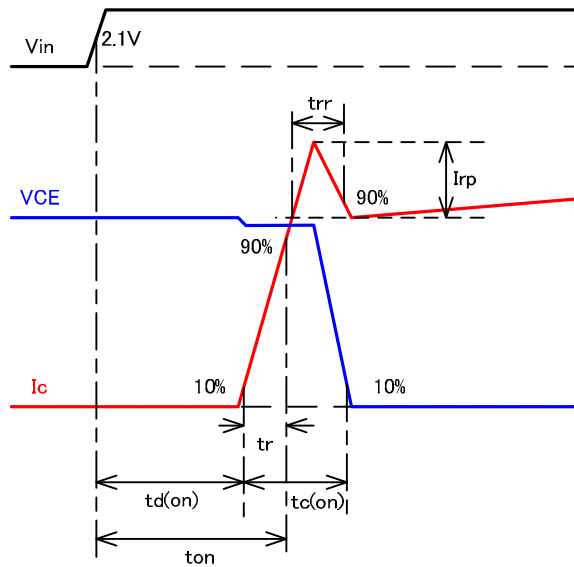
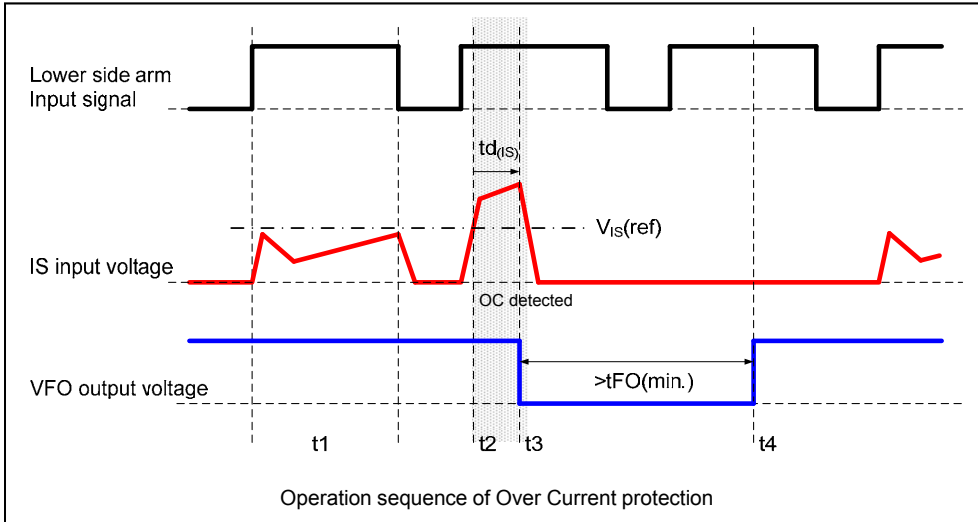


Fig.2-2: Operation sequence of Over current protection



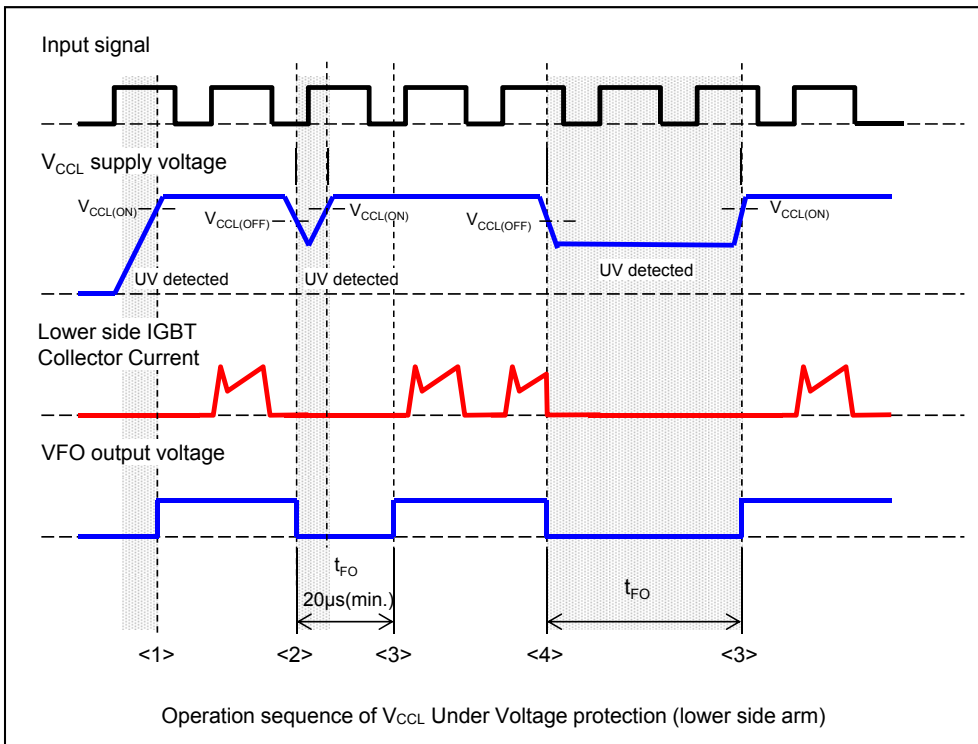
t1: IS input voltage does not exceed $V_{IS(ref)}$, while the collector current of the lower side IGBT is under the normal operation.

t2: When IS input voltage exceeds $V_{IS(ref)}$, the OC is detected.

t3: The fault output VFO is activated and all lower side IGBT shut down simultaneously after the over current protection delay time $td_{(IS)}$. Inherently there is dead time of LVIC in $td_{(IS)}$.

t4: After the fault output pulse width t_{FO} , the OC is reset. Then next input signal is activated.

Fig.2-3: Operation sequence of V_{CCL} Under voltage trip (lower side arm)



When V_{CCL} is under 4V, UV and fault output are not activated.

<1> When V_{CCL} is under $V_{CCL(ON)}$, all lower side IGBTs are OFF state.

After V_{CCL} rises $V_{CCL(ON)}$, the fault output VFO is released (high level).

And the LVIC starts to operate, then next input is activated.

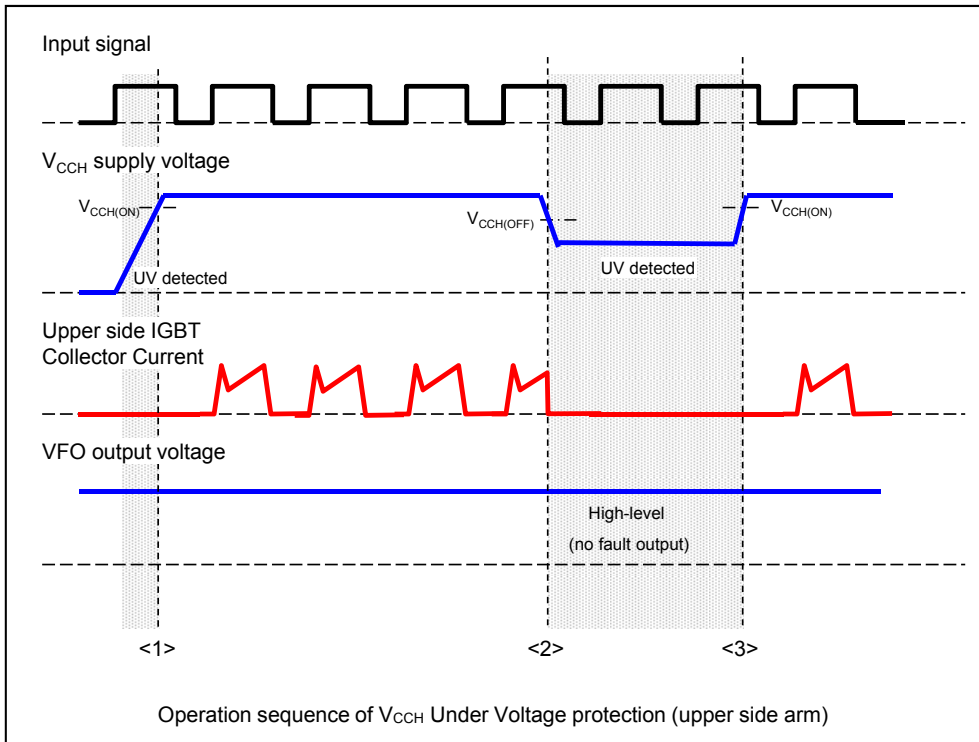
<2> The fault output VFO is activated when V_{CCL} falls below $V_{CCL(OFF)}$, and all lower side IGBT remains OFF state.

When the voltage drop time is less than $20\mu s$, the fault output pulse width is generated minimum $20\mu s$ and all lower side IGBTs are OFF state in spite of input signal condition during that time.

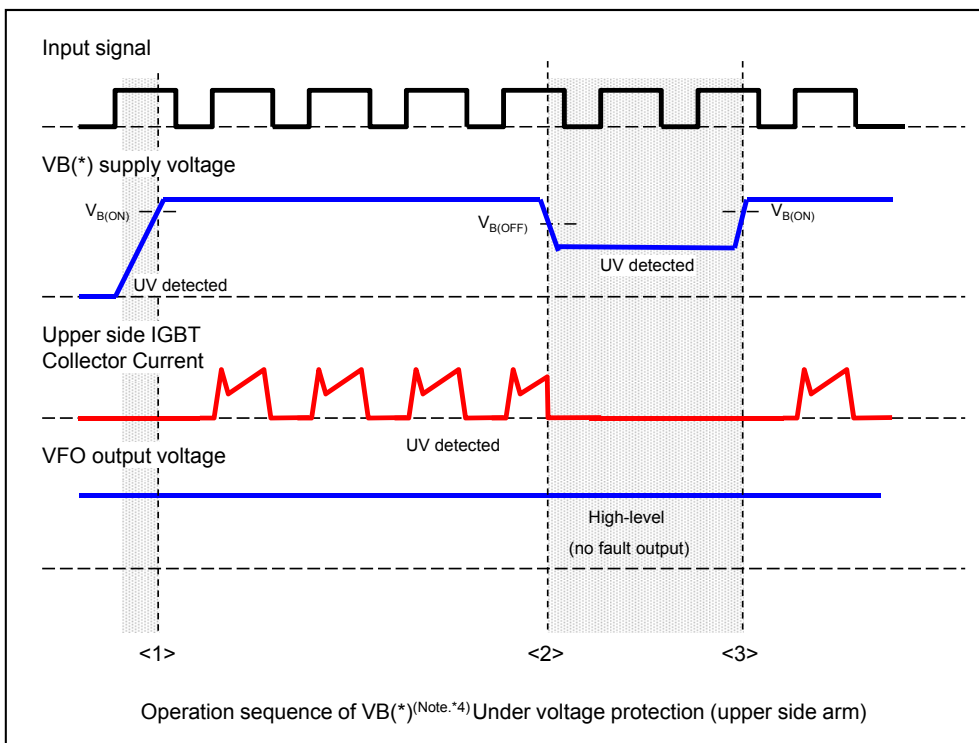
<3> UV is reset after t_{FO} when V_{CCL} exceeds $V_{CCL(ON)}$ and the fault output VFO is reset simultaneously.

And the LVIC starts to operate, then next input is activated.

<4> When the voltage drop time is more than t_{FO} , the fault output pulse width is generated and all lower side IGBTs are OFF state in spite of input signal condition during the same time.

Fig.2-4: Operation sequence of V_{CCH} Under voltage trip (upper side arm)

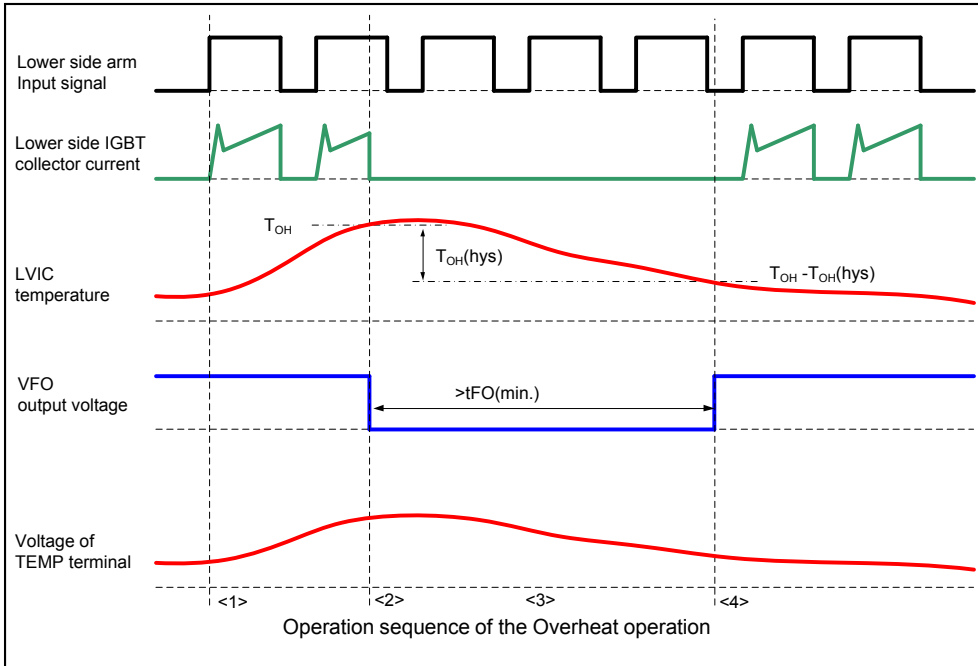
- <1> When V_{CCH} is under $V_{CCH(ON)}$, the upper side IGBT is OFF state.
After V_{CCH} exceeds $V_{CCH(ON)}$, the HVIC starts to operate. Then next input is activated.
The fault output VFO is constant (high level) not to depend on V_{CCH} .
- <2> After V_{CCH} falls below $V_{CCH(OFF)}$, the upper side IGBT remains OFF state.
But the fault output VFO keeps high level.
- <3> The HVIC starts to operate after UV is reset, then next input is activated.

Fig.2-5: Operation sequence of V_B Under voltage trip (upper side arm)

- <1> When $V_B(*)$ is under $V_B(ON)$, the upper side IGBT is OFF state.
After $V_B(*)$ exceeds $V_B(ON)$, the HVIC starts to operate. Then next input is activated.
The fault output VFO is constant (high level) not to depend on $V_B(*)$. (Note.*14)
- <2> After $V_B(*)$ falls below $V_B(OFF)$, the upper side IGBT remains OFF state.
But the fault output VFO keeps high level.
- <3> The HVIC starts to operate after UV is reset, then next input is activated.

Note *14: The fault output is not given HVIC bias conditions.

Fig.2-6: Overheat protection



This function is applied to "6MBP**VXF060-50".

The IPM has the over-heating protection (OH) function by monitoring the LVIC temperature.

The T_{OH} sensor position is shown in Fig.1-1.

<1> The collector current of the lower side IGBT is under the normal operation while the LVIC temperature does not exceed T_{OH} .

<2> The IPM shutdown all lower side IGBTs while the LVIC temperature exceeds T_{OH} .

<3> The TEMP terminal continue to output the voltage which correspond to temperature of LVIC even if IPM is in OH condition.

<4> The fault status is reset when the LVIC temperature drops below $(T_{OH} - T_{OH(hys)})$. The all lower side IGBTs restarted to normal operation.

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Information

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7 AT-NPC 3-Level 損失シミュレーションソフト	www.fujielectric.co.jp/products/semiconductor/model/igbt/simulation_3level/
8 富士電機技報	www.fujielectric.co.jp/products/semiconductor/journal/
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10 改廃のお知らせ	www.fujielectric.co.jp/products/semiconductor/discontinued/

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3 Application Manuals	www.fujielectric.com/products/semiconductor/model/igbt/application/
4 Technical Documents	www.fujielectric.com/products/semiconductor/model/igbt/technical/
5 Mounting Instructions	www.fujielectric.com/products/semiconductor/model/igbt/mounting/
6 IGBT Loss Simulation Software	www.fujielectric.com/products/semiconductor/model/igbt/simulation/
7 AT-NPC 3-Level Loss Simulation Software	www.fujielectric.com/products/semiconductor/model/igbt/simulation_3level/
8 Fuji Electric Journal	www.fujielectric.com/products/semiconductor/journal/
9 Contact	www.fujielectric.com/products/semiconductor/contact/
10 Revised and discontinued product information	www.fujielectric.com/products/semiconductor/discontinued/

中国

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